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Vishay Siliconix

Automotive N-Channel 80 V (D-S) 175 °C MOSFET



PRODUCT SUMMARY				
V _{DS} (V)	80			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.0032			
I _D (A)	120			
Configuration	Single			
Package	TO-263			

FEATURES

- TrenchFET® power MOSFET
- Package with low thermal resistance
- AEC-Q101 qualified d
- 100 % R_a and UIS tested
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>



G O	
N-Channel MOSFET	O _S

ORDERING INFORMATION			
Lead (Pb)-free and halogen-free	SQM60030E_GE3		

PARAMETER PARAMETER	()	SYMBOL	LIMIT	UNIT	
				UNII	
Drain-source voltage		V_{DS}	80	V	
Gate-source voltage		V_{GS}	± 20	V	
Continuous drain current a	T _C = 25 °C	l _D	120		
Continuous drain current ~	T _C = 125 °C		120		
Continuous source current (diode conduction) a		I _S	120	Α	
Pulsed drain current ^b		I _{DM}	250		
Single pulse avalanche current		I _{AS}	70		
Single pulse avalanche Energy	L = 0.1 mH	E _{AS}	245	mJ	
	T _C = 25 °C	Б	375	W	
Maximum power dissipation ^b	T _C = 125 °C	P_{D}	125	VV	
Operating junction and storage temperatur	e range	T _J , T _{sta}	-55 to +175	°C	

THERMAL RESISTANCE RATINGS						
PARAMETER		SYMBOL	LIMIT	UNIT		
Junction-to-ambient P	CB mount c	R_{thJA}	40	°C/W		
Junction-to-case (drain)		R _{thJC}	0.4	- C/VV		

Notes

- a. Package limited
- b. Pulse test; pulse width $\leq 300 \,\mu\text{s}$, duty cycle $\leq 2 \,\%$
- c. When mounted on 1" square PCB (FR4 material)
- d. Parametric verification ongoing



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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static	•							
Drain-source breakdown voltage	V _{DS}	$V_{GS} = 0$, $I_D = 250 \mu A$		80	-	-	V	
Gate-source threshold voltage	V _{GS(th)}	V _{DS} =	· V _{GS} , I _D = 250 μA	2.5	3	3.5	V	
Gate-source leakage	I _{GSS}	V _{DS} =	$0 \text{ V}, \text{ V}_{GS} = \pm 20 \text{ V}$	-	-	± 100	nA	
		V _{GS} = 0 V	V _{DS} = 80 V	-	-	1	1	
Zero gate voltage drain current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 80 V, T _J = 125 °C	-	-	50	μΑ	
		V _{GS} = 0 V	V _{DS} = 80 V, T _J = 175 °C	-	-	800	1	
On-state drain current a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 \text{ V}$	120	-	-	Α	
		V _{GS} = 10 V	I _D = 30 A	-	0.0026	0.0032		
Drain-source on-state resistance a	R _{DS(on)}	V _{GS} = 10 V	I _D = 30 A, T _J = 125 °C	-	-	0.0051	Ω	
	, ,	V _{GS} = 10 V	I _D = 30 A, T _J = 175 °C	-	-	0.0062	•	
Forward transconductance b	9 _{fs}	V _{DS} = 15 V, I _D = 30 A		-	105	-	S	
Dynamic ^b								
Input capacitance	C _{iss}			-	9500	12 000		
Output capacitance	C _{oss}	$V_{GS} = 0 V$	V _{GS} = 0 V V _{DS} = 25 V, f = 1 MHz		3300	4500	pF	
Reverse transfer capacitance	C _{rss}			-	310	400		
Total gate charge ^c	Qg			-	110	165		
Gate-source charge ^c	Q_{gs}	V _{GS} = 10 V	$V_{DS} = 40 \text{ V}, I_{D} = 80 \text{ A}$	-	35	-	nC	
Gate-drain charge ^c	Q_{gd}			-	15	-		
Gate resistance	R _g		f = 1 MHz	0.7	1.45	2.2	Ω	
Turn-on delay time ^c	t _{d(on)}			-	19	30		
Rise time ^c	t _r	$V_{DD} = 40 \text{ V}, \text{ R}_{L} = 0.5 \Omega$ $I_{D} \cong 80 \text{ A}, \text{ V}_{GEN} = 10 \text{ V}, \text{ R}_{g} = 1 \Omega$		-	13	20	ns	
Turn-off delay time ^c	t _{d(off)}			-	39	60	115	
Fall time ^c	t _f			-	9	15		
Source-Drain Diode Ratings and Char	acteristics ^b				•			
Pulsed current ^a	I _{SM}			-	-	250	Α	
Forward voltage	V_{SD}	I _F = 80 A, V _{GS} = 0 V		_	0.9	1.5	V	

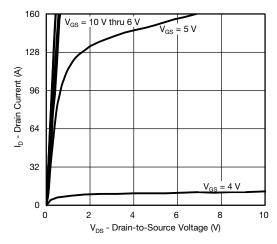
Notes

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%$
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

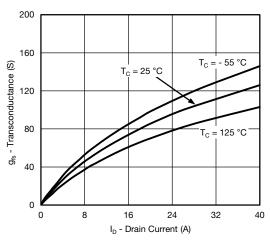
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



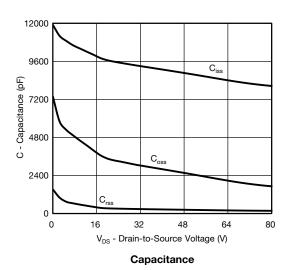
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

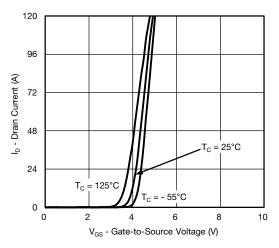


Output Characteristics

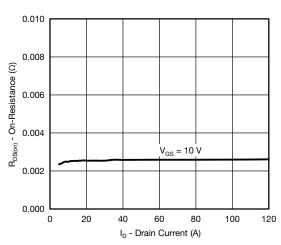


Transconductance

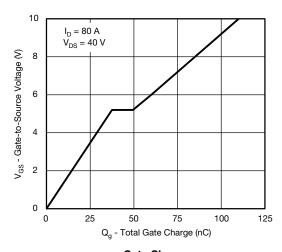




Transfer Characteristics

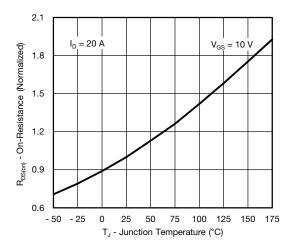


On-Resistance vs. Drain Current

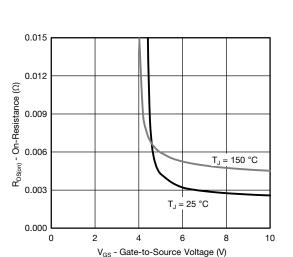




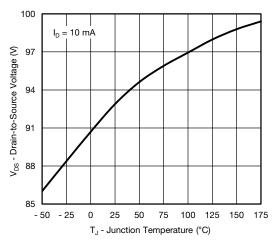
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



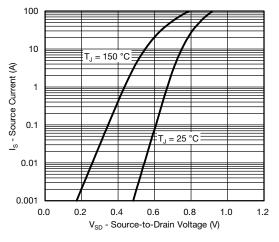
On-Resistance vs. Junction Temperature



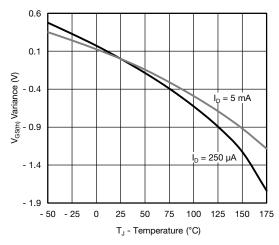
On-Resistance vs. Gate-to-Source Voltage



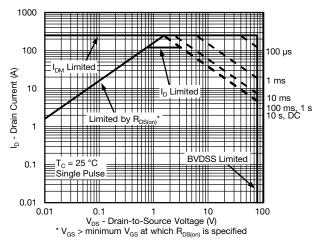
Drain Source Breakdown vs. Junction Temperature



Source Drain Diode Forward Voltage



Threshold Voltage

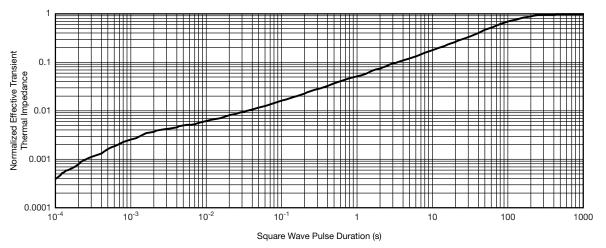


Safe Operating Area

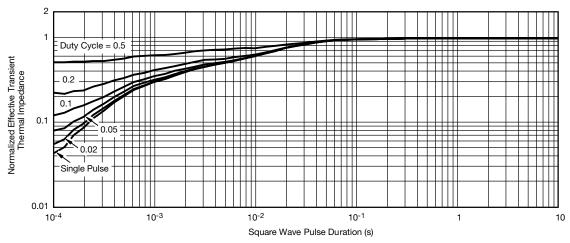
For technical questions, contact: automostechsu



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

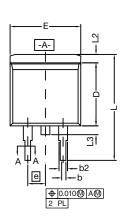
Note

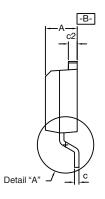
- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction to Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction to Case (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

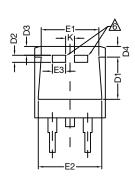
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TO-263 (D²PAK): 3-LEAD

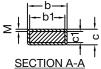








DETAIL A (ROTATED 90°)



<u> </u>	b	+ +
≥		<u>, o</u>
0	ECTION A	1

- 1. Plane B includes maximum features of heat sink tab and plastic.
- 2. No more than 25 % of L1 can fall above seating plane by max. 8 mils.
- 3. Pin-to-pin coplanarity max. 4 mils.
- 4. *: Thin lead is for SUB, SYB. Thick lead is for SUM, SYM, SQM.
- 5. Use inches as the primary measurement.

6 This feature is for thick lead.

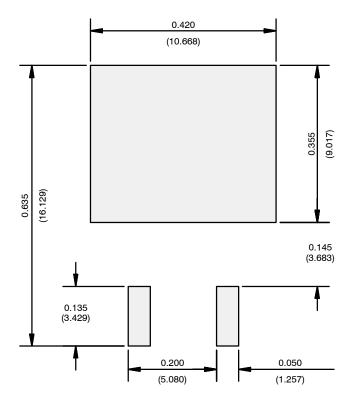
		INC	HES	MILLIMETERS		
	DIM.	MIN.	MAX.	MIN.	MAX.	
Α		0.160	0.190	4.064	4.826	
	b	0.020	0.039	0.508	0.990	
	b1	0.020	0.035	0.508	0.889	
	b2	0.045	0.055	1.143	1.397	
c*	Thin lead	0.013	0.018	0.330	0.457	
	Thick lead	0.023	0.028	0.584	0.711	
c1	Thin lead	0.013	0.017	0.330	0.431	
CI	Thick lead	0.023	0.027	0.584	0.685	
	c2	0.045	0.055	1.143	1.397	
	D	0.340	0.380	8.636	9.652	
	D1	0.220	0.240	5.588	6.096	
	D2	0.038	0.042	0.965	1.067	
	D3	0.045	0.055	1.143	1.397	
	D4	0.044	0.052	1.118	1.321	
	E	0.380	0.410	9.652	10.414	
	E1	0.245	-	6.223	-	
	E2	0.355	0.375	9.017	9.525	
	E3	0.072	0.078	1.829	1.981	
	е	0.100	BSC	2.54 BSC		
	K	0.045	0.055	1.143	1.397	
L		0.575	0.625	14.605	15.875	
L1		0.090	0.110	2.286	2.794	
L2		0.040	0.055	1.016	1.397	
L3		0.050	0.070	1.270	1.778	
L4		0.010	BSC	0.254 BSC		
	М	-	0.002	-	0.050	
ECN: T13-0707-Rev. K, 30-Sep-13						

DWG: 5843





RECOMMENDED MINIMUM PADS FOR D²PAK: 3-Lead



Recommended Minimum Pads Dimensions in Inches/(mm)

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